Substitute Form PTO-1449 (Modified)

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Information Disclosure Statement by Applicant
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(37 CFR §1.98(b))

Attorney's Docket No.	Application No.
07977-004002	New Continuation Application
Applicant	
Naoto Kusumoto et al.	
Filing Date	**Group Art Unit**
June 25, 2003	

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
DM	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
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DM	AT	6,358,784	03/19/2002	Zhang, et al			

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation Yes	Translation No
DM	AU	ZA8306334	03/1984	China				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
DM	AX	3-286518	12/1991	Japan				

Examiner Signature	Date Considered
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DPR	AY	4-307727	10/1992	Japan	—	—		—

Other Documents (include Author, Title, Date, and Place of Publication)

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DPR	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi..."; *MRS Symp. Proc. 343*; pp. 709; 1994
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	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", Appl. Phys. Lett., Vol. 66, No. 11, pp. 1394-1396
	ACC	Caune et al.; "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; *Appl. Surf. Sci. 36*; p. 597; 1989
	ADD	Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; *IEEE IEDM*; pp. 829-832; 1995
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	AHH	Kuriyama et al.; "Improving...ELA method for giant microelectronics"; *Jpn. J. Appl. Phys. 31(12B)*; p. 4550; December 1992
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[signature]	8/05

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